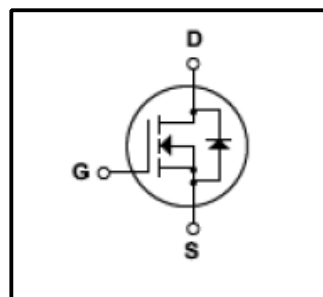


Silicon N-Channel MOSFET

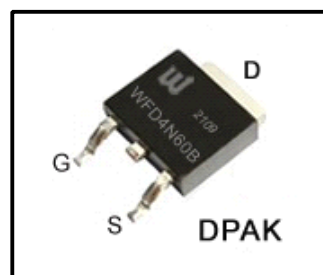
Features

- 4A,600V. $R_{DS(on)}$ (Max 2.4 Ω)@ $V_{GS}=10V$
- Ultra-low Gate Charge(Typical 16nC)
- Fast Switching Capability
- 100%Avalanche Tested
- Isolation Voltage (VISO = 4000V AC)
- Maximum Junction Temperature Range(150℃)



General Description

This Power MOSFET is produced using Winsemi's advanced planar stripe, DMOS technology. This latest technology has been especially designed to minimize on-state resistance, have a high Rugged avalanche characteristics. This devices is specially well Suited for half bridge and full bridge resonant topology line a electronic lamp ballast.



Absolute Maximum Ratings

Symbol	Parameter	Value	Units
V_{DSS}	Drain Source Voltage	600	V
I_D	Continuous Drain Current(@ $T_c=25^\circ C$)	4	A
	Continuous Drain Current(@ $T_c=100^\circ C$)	2.5	A
I_{DM}	Drain Current Pulsed (Note1)	16	A
V_{GS}	Gate to Source Voltage	± 30	V
E_{AS}	Single Pulsed Avalanche Energy (Note 2)	240	mJ
E_{AR}	Repetitive Avalanche Energy (Note 1)	10	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	4.5	V/ns
P_D	Total Power Dissipation(@ $T_c=25^\circ C$)	80	W
	Derating Factor above 25℃	0.78	W/℃
T_J, T_{stg}	Junction and Storage Temperature	-55~150	℃
T_L	Channel Temperature	300	℃

Thermal Characteristics

Symbol	Parameter	Value			Units
		Min	Typ	Max	
R_{QJC}	Thermal Resistance, Junction-to-Case	-	-	1.56	℃/W
R_{QJA}	Thermal Resistance, Junction-to-Ambient*			50	
R_{QJA}	Thermal Resistance, Junction-to-Ambient	-	-	110	℃/W

*When mounted on the minimum pad size recommended(PCB Mount)

Electrical Characteristics (T_c = 25° C)

Characteristics		Symbol	Test Condition	Min	Type	Max	Unit
Gate leakage current		I _{GSS}	V _{GS} = ±30 V, V _{DS} = 0 V	-	-	±100	nA
Gate-source breakdown voltage		V _{(BR)GSS}	I _G = ±10 μA, V _{DS} = 0 V	±30	-	-	V
Drain cut-off current		I _{DSS}	V _{DS} = 600 V, V _{GS} = 0 V	-	-	10	μA
			V _{DS} = 480 V, T _c = 125°C	-	-	100	μA
Drain-source breakdown voltage		V _{(BR)DSS}	I _D = 250 μA, V _{GS} = 0 V	600	-	-	V
Gate threshold voltage		V _{GS(th)}	V _{DS} = 10 V, I _D =250 μA	2	-	4	V
Drain-source ON resistance		R _{DS(ON)}	V _{GS} = 10 V, I _D =2.0A	-	1.7	2.4	Ω
Input capacitance		C _{iSS}	V _{DS} = 25 V, V _{GS} = 0 V, f = 1 MHz	-	545	670	pF
Reverse transfer capacitance		C _{rSS}		-	7	10	
Output capacitance		C _{oss}		-	70	90	
Switching time	Rise time	tr	V _{DD} =300 V, I _D = 4.0A R _G =25 Ω (Note4,5)	-	10	30	ns
	Turn-on time	ton		-	35	80	
	Fall time	tf		-	45	100	
	Turn-off time	toff		-	20	50	
Total gate charge (gate-source plus gate-drain)		Qg	V _{DD} = 480 V, V _{GS} = 10 V, I _D =4.0A (Note4,5)	-	16	20	nC
Gate-source charge		Qgs		-	3.4	-	
Gate-drain ("miller") Charge		Qgd		-	7	-	

Source-Drain Ratings and Characteristics (T_a = 25° C)

Characteristics	Symbol	Test Condition	Min	Type	Max	Unit
Continuous drain reverse current	I _{DR}	-	-	-	4	A
Pulse drain reverse current	I _{DRP}	-	-	-	17.6	A
Forward voltage (diode)	V _{DSF}	I _{DR} = 4.0 A, V _{GS} = 0 V	-	-	1.4	V
Reverse recovery time	trr	I _{DR} = 4.0 A, V _{GS} = 0 V,	-	390	-	ns
Reverse recovery charge	Q _{rr}	dI _{DR} / dt = 100 A / μs	-	2.2	-	μC

Note 1.Repeativity rating :pulse width limited by junction temperature

2.L=18.5mH,I_{AS}=4.0A,V_{DD}=50V,R_G=0Ω,Starting T_J=25°C

3.I_{SD}≤4A,di/dt≤200A/us, V_{DD}<BV_{DSS},STARTING T_J=25°C

4.Pulse Test: Pulse Width≤300us,Duty Cycles≤2%

5.Essentially independent of operating temperature.

This transistor is an electrostatic sensitive device

Please handle with caution

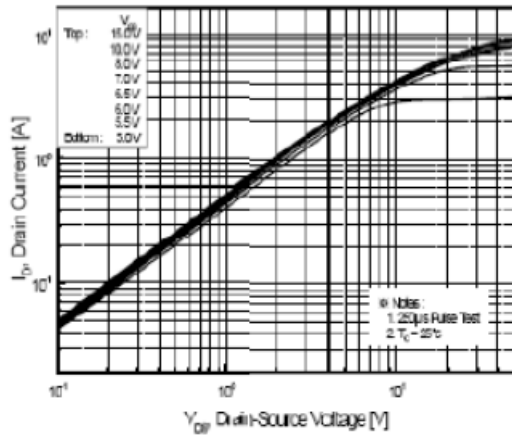


Fig.1 On-State Characteristics

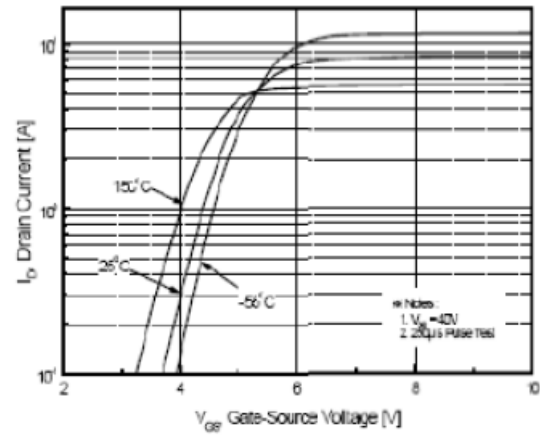


Fig.2 Transfer Current characteristics

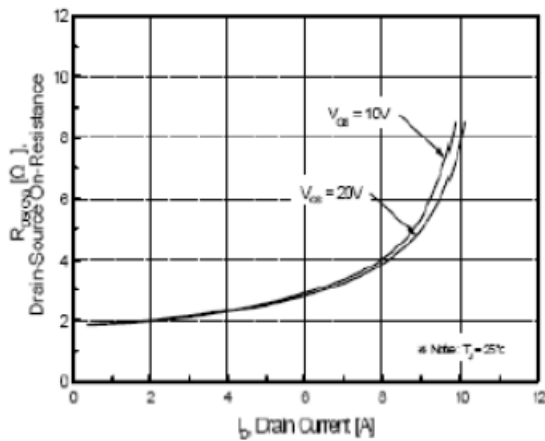


Fig.3. On Resistance Variation vs Drain current

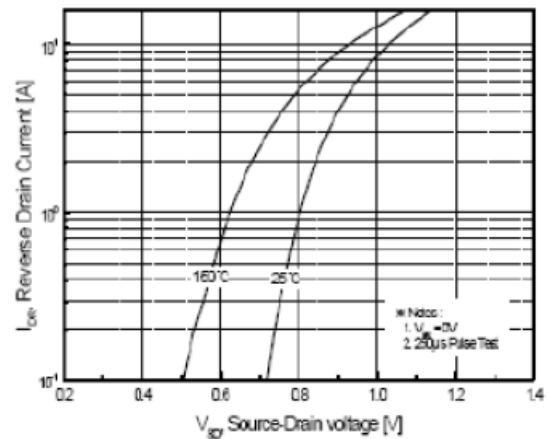


Fig.4 Body Diode Forward Voltage Variation vs Source Current and Temperature

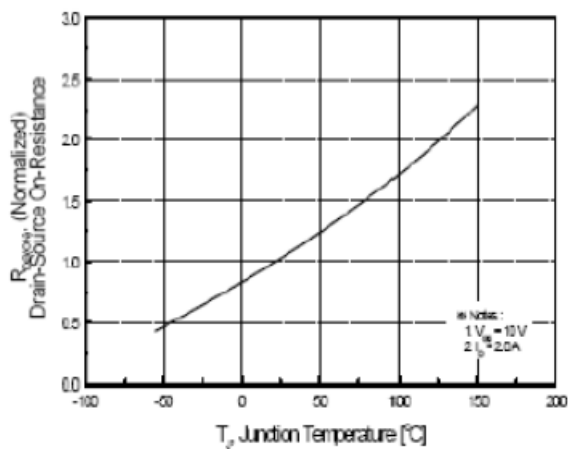


Fig.5 On-Resistance Variation vs Junction Temperature

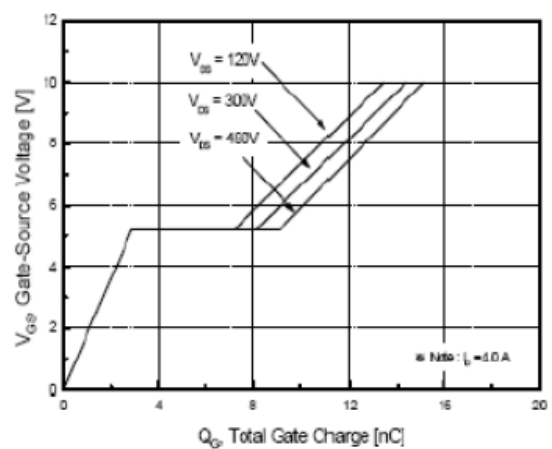


Fig.6 Gate Charge Characteristics

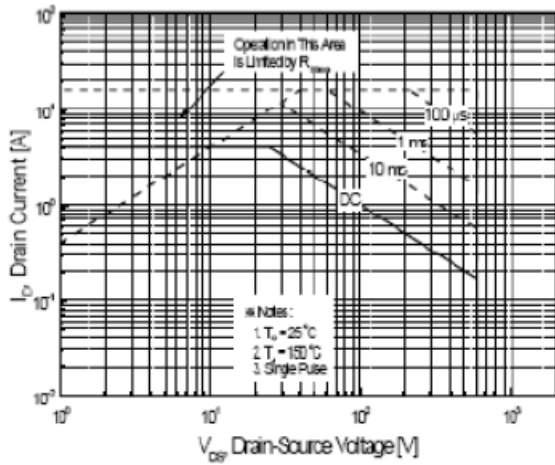


Fig.7 Maximum Safe Operation Area

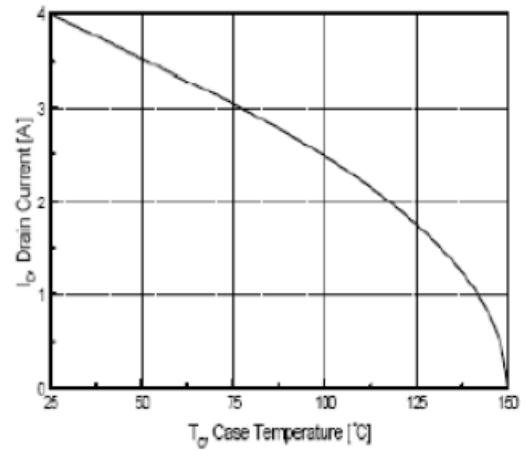


Fig.8 Maximum Drain Current vs. Case Temperature

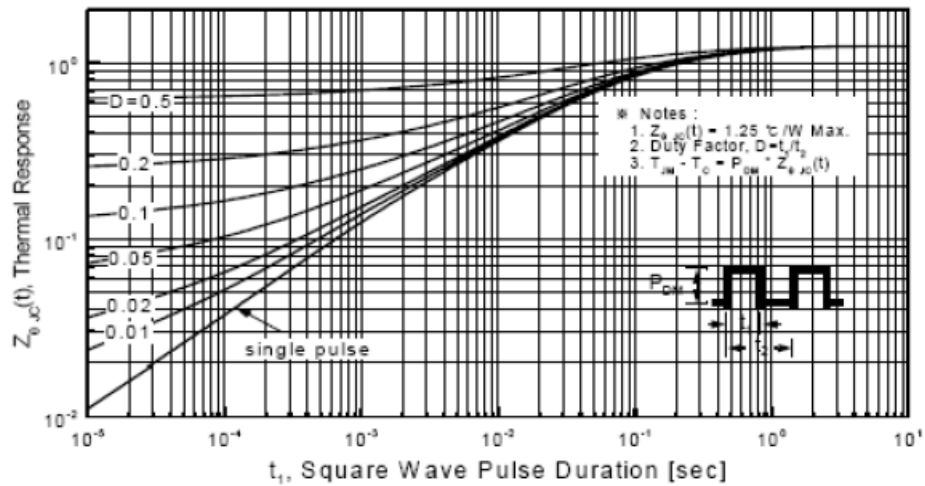


Fig.9 Transient Thermal Response curve

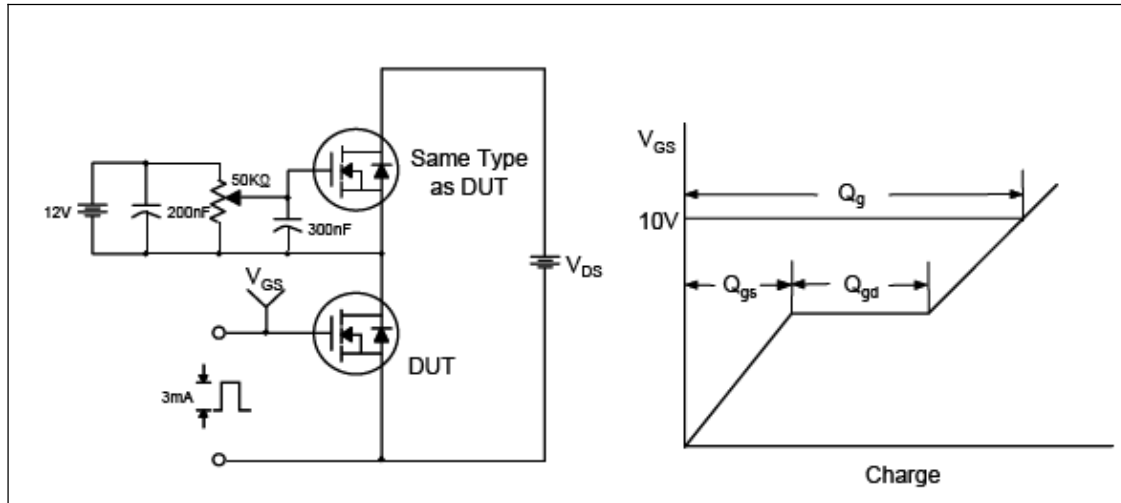


Fig.10 Gate Test Circuit & Waveform

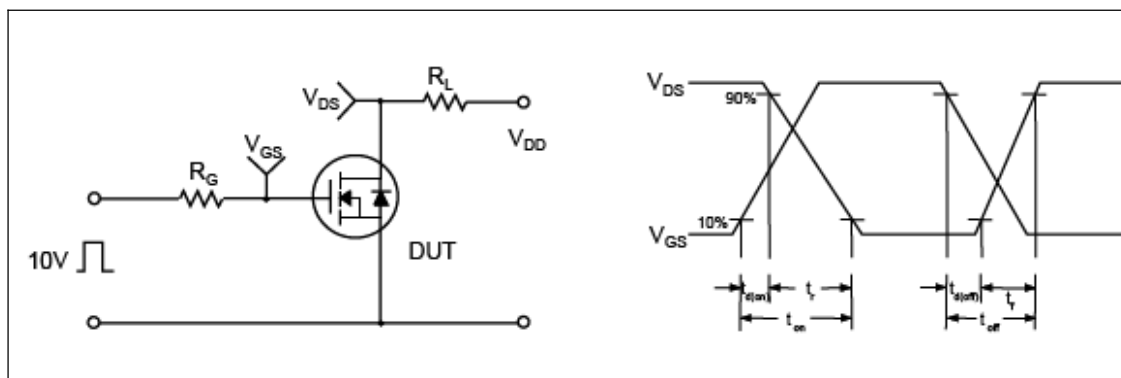


Fig.11 Resistive Switching Test Circuit & Waveform

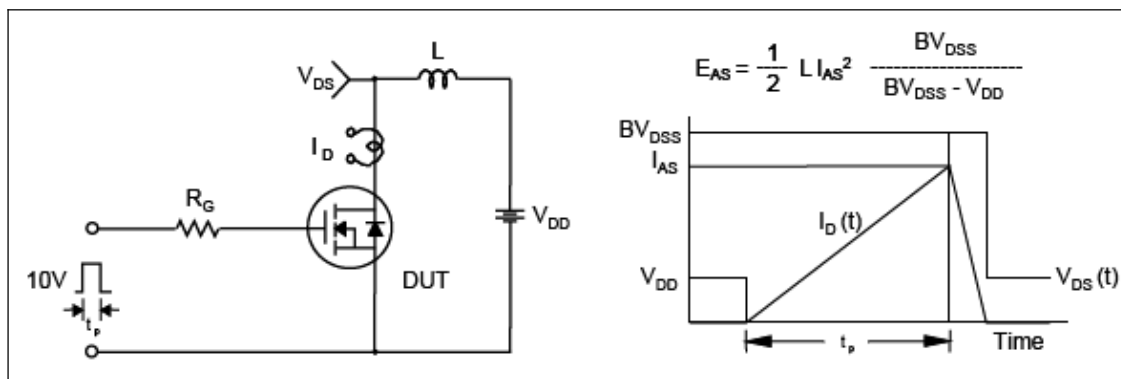


Fig.12 Unclamped Inductive Switching Test Circuit & Waveform

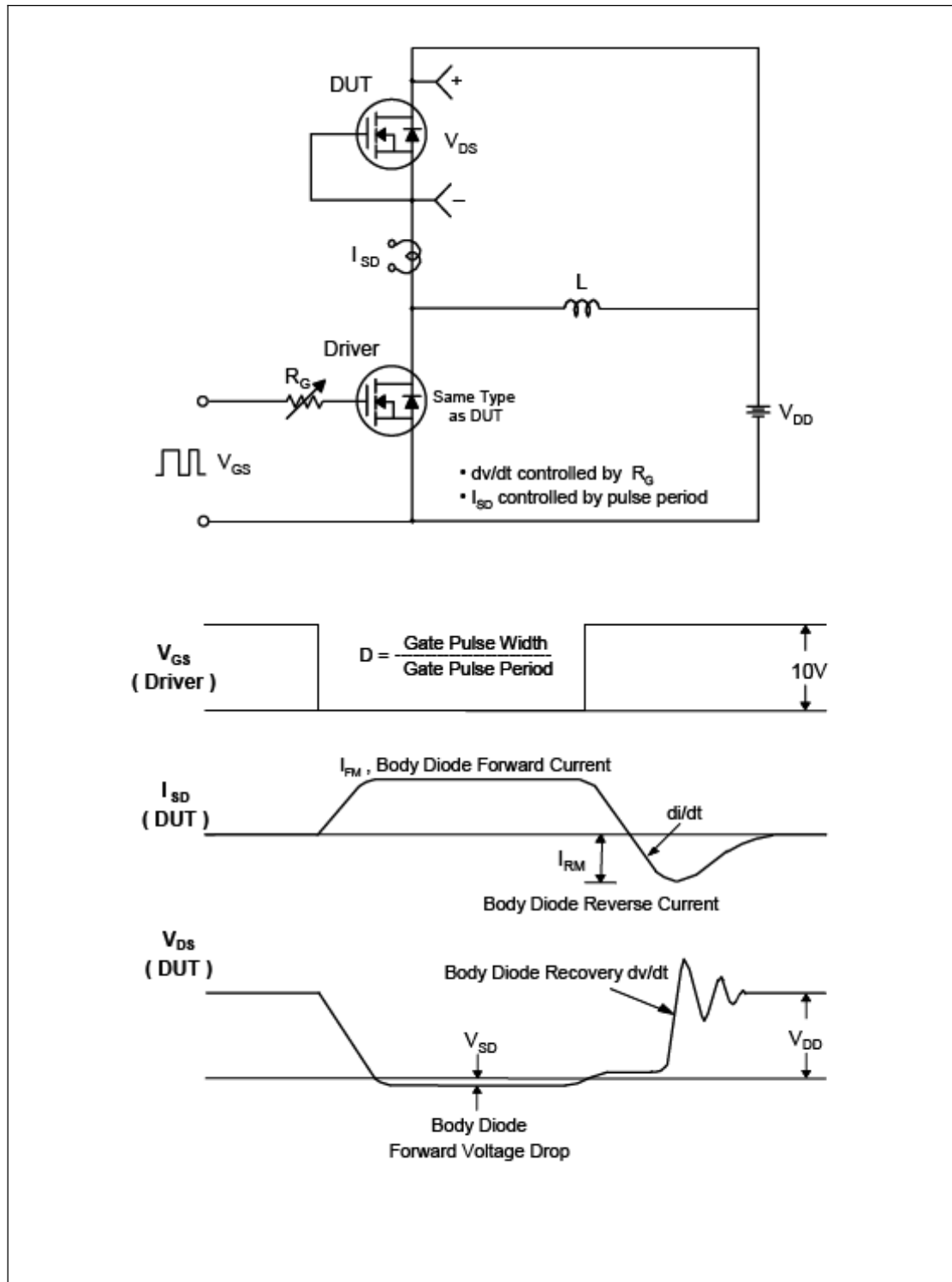


Fig.13 Peak Diode Recovery dv/dt Test Circuit & Waveform

TO-252 Package Dimension

Unit:mm

